

UTC UNISONIC TECHNOLOGIES CO., LTD

BU407

NPN SILICON TRANSISTOR

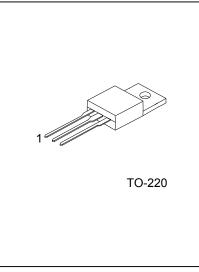
NPN EXPITAXIAL PLANAR TRANSISTOR

DESCRIPTION

The UTC BU407 is a NPN epitaxial planar transistor, designed for use in TV Horizontal output and switching applications.

FEATURES

* High breakdown voltage



Lead-free: BU407L Halogen-free: BU407G

ORDERING INFORMATION

Ordering Number			Pin Assignment			Deaking		
Normal	Lead Free Plating	Halogen Free	Package	1	2	3	Packing	
BU407-x-TA3-T	BU407L-x-TA3-T	BU407G-x-TA3-T	TO-220	В	С	Е	Tube	

BU407L-x-AE3-T	(1)Packing Type (2)Package Type (3)Rank	 (1) T: Tube (2) TA3: TO-220 (3) x: refer to Classification of h_{EE2}
	(3)Rank	(3) x: refer to Classification of h_{FE2}
	(4)Lead Plating	(4) G: Halogen Free, L: Lead Free, Blank: Pb/Sn

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector Base Voltage	V _{CBO}	330	V
Collector to Emitter Voltage	V _{CEO}	150	V
Emitter to Base Voltage	V _{EBO}	6	V
Collector Current	lc	7	А
Base Current	I _B	4	А
Collector Dissipation ($T_a = 25^{\circ}C$)	Pc	60	W
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient	θ _{JA}			70	°C/W
Junction to Case	θ _{JC}			2.08	°C/W

■ ELECTRICAL CHARACTERISTICS (T_a=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Emitter Sustaining Voltage	BV _{CEO}	I _C =100 mA, I _B = 0	150			V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}			1	V	
Base-Emitter On Voltage	V _{BE(SAT)}	$-I_{\rm C} = 5 \text{A}, I_{\rm B} = 0.5 \text{A}$			1.2	V
Collect Cutoff Current'	I _{CES}	V _{CE} =400 V			5	mA
Emitter Cutoff Current	I _{EBO}	$V_{BE} = 6 V, I_{C} = 0$			1	mA
	h _{FE1}	I _C = 500 mA, V _{CE} = 5 V	25			
DC Current Gain	h _{FE2}	$I_{C} = 2 A, V_{CE} = 5 V$	35		200	
	h _{FE3}	$I_{C} = 5 \text{ A}, V_{CE} = 5 \text{ V}$	10			
Current Gain Bandwidth Product	f_{T}	I _C = 500 mA, V _{CE} = 10 V, f =1 MHz	10			MHz

CLASSIFICATION OF h_{FE2}

RANK	В	С	D
RANGE	35-85	75-125	115-200

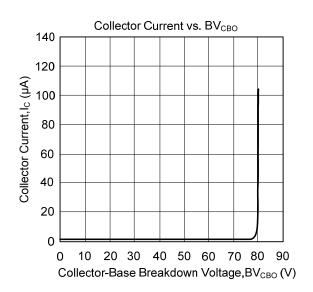


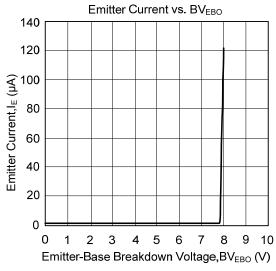
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NPN EPITAXIAL SILICON TRANSISTOR

Collector Current vs. BV_{CEO}

TYPICAL CHARACTERISTICS





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